

IRFH8324TR2PBF

IRFH8324TR2PBF Information



For Reference Only

Part Number IRFH8324TR2PBF
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 18A 5X6 PQFN

Package 8-PowerTDFN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRFH8324TR2PBF Specifications

Manufacturer Part Number IRFH8324TR2PBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-PowerTDFN Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 23A (Ta), 90A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.35V @ 50µA Gate Charge (Qg) (Max) @ Vgs 31nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2380pF @ 10V Vgs (Max) ± 2V FET Feature - Power Dissipation (Max) 3.6W (Ta), 54W (Tc) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 8-PowerTDFN Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 23A (Ta), 90A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 31nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ### 20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature Supplier Device Package PQFN (5x6) Package / Case B-PowerTDFN	Manufacturer Part Number	IRFH8324TR2PBF
Package 8-PowerTDFN Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 23A (Ta), 90A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.35V @ 50μA Gate Charge (Qg) (Max) @ Vgs 31nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2380pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.6W (Ta), 54W (Tc) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN	Manufacturer	Infineon Technologies
Package 8-PowerTDFN Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 23A (Ta), 90A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.35V @ 50µA Gate Charge (Qg) (Max) @ Vgs 31nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2380pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.6W (Ta), 54W (Tc) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN	Category	Discrete Semiconductor Products
Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 23A (Ta), 90A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.35V @ 50μA Gate Charge (Qg) (Max) @ Vgs 31nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2380pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.6W (Ta), 54W (Tc) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 23A (Ta), 90A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.35V @ 50µA Gate Charge (Qg) (Max) @ Vgs 31nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2380pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.6W (Ta), 54W (Tc) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN	Package	8-PowerTDFN
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C23A (Ta), 90A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.35V @ 50μAGate Charge (Qg) (Max) @ Vgs31nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2380pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.6W (Ta), 54W (Tc)Rds On (Max) @ Id, Vgs4.1 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePQFN (5x6)Package / Case8-PowerTDFN	Series	HEXFET?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C23A (Ta), 90A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.35V @ 50μAGate Charge (Qg) (Max) @ Vgs31nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2380pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.6W (Ta), 54W (Tc)Rds On (Max) @ Id, Vgs4.1 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePQFN (5x6)Package / Case8-PowerTDFN	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature Supplier Device Package Package / Case 23A (Ta), 90A (Tc) 4.5V, 10V 2.35V @ 50µA 31nC @ 10V 2380pF @ 10V **EOV **EOV	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs All mOhm @ 20A, 10V Operating Temperature Surplier Device Package Package / Case 4.5V, 10V 2.35V @ 50μA 3.1nC @ 10V 2.380pF @ 10V 4.20V 4.1 mOhm @ 20A, 10V CPS (TJ) Surface Mount Surface Mount PQFN (5x6) 8-PowerTDFN	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id 2.35V @ 50μA Gate Charge (Qg) (Max) @ Vgs 31nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2380pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.6W (Ta), 54W (Tc) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN	Current - Continuous Drain (Id) @ 25°C	23A (Ta), 90A (Tc)
Gate Charge (Qg) (Max) @ Vgs 31nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2380pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.6W (Ta), 54W (Tc) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-PowerTDFN	Vgs(th) (Max) @ Id	2.35V @ 50μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)3.6W (Ta), 54W (Tc)Rds On (Max) @ Id, Vgs4.1 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePQFN (5x6)Package / Case8-PowerTDFN	Gate Charge (Qg) (Max) @ Vgs	31nC @ 10V
FET Feature - Power Dissipation (Max) 3.6W (Ta), 54W (Tc) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN	Input Capacitance (Ciss) (Max) @ Vds	2380pF @ 10V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.1 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs4.1 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePQFN (5x6)Package / Case8-PowerTDFN	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN	Power Dissipation (Max)	3.6W (Ta), 54W (Tc)
Mounting Type Surface Mount Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN	Rds On (Max) @ Id, Vgs	4.1 mOhm @ 20A, 10V
Supplier Device Package PQFN (5x6) Package / Case 8-PowerTDFN	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-PowerTDFN	Mounting Type	Surface Mount
	Supplier Device Package	PQFN (5x6)
Report errors?	Package / Case	8-PowerTDFN
		Report errors?

IRFH8324TR2PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFH8324TR2PBF Payment Methods



















IRFH8324TR2PBF Shipping Methods













If you have any question about IRFH8324TR2PBF, please do not hesitate to contact us!

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